优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25°C$ (Notes 5 & 7)
Q1	30V	32mΩ @ V_{GS} = 10V	8.1A
		46mΩ @ V_{GS} = 4.5V	6.1A
Q2	-30V	39mΩ @ V_{GS} = -10V	-7A
		53mΩ @ V_{GS} = -4.5V	-5.6A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch
- Load Switch

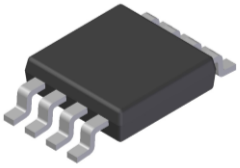
Features

- Low On-Resistance
- N-Channel: 32mΩ @ 10V
  46mΩ @ 4.5V
- P-Channel: 39mΩ @ -10V
  53mΩ @ -4.5V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
  Complementary Pair MOSFET

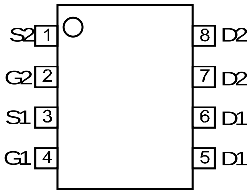
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 ⓔ3
- Marking Information (See Page 2)
- Ordering Information
- Weight: 0.072 grams (Approximate)

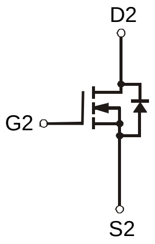
SO-8



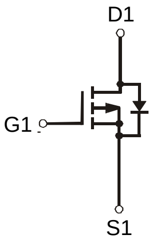
Top View



Top View

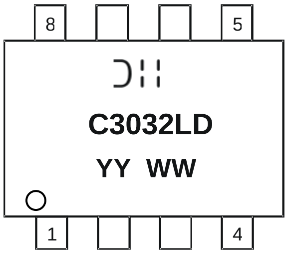


N-Channel MOSFET



P-Channel MOSFET

Marking Information



Ↄ¦¦ = Manufacturer's Marking
C3032LD = Product Type Marking Code
YYWW = Date Code Marking
YY or $\overline{YY}$ = Year (ex: 18 = 2018)
WW = Week (01 to 53)

Maximum Ratings N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C	I_D	8.1	A
		T_A = +85°C		5.1	
Pulsed Drain Current (Note 6)			I_{DM}	25	A

Maximum Ratings P-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C	I_D	-7.0	A
		T_A = +85°C		-4.5	
Pulsed Drain Current (Note 6)			I_{DM}	-25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	50	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	1.45	2.1	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	23	32	mΩ	V_{GS} = 10V, I_D = 7A
			32	46		V_{GS} = 4.5V, I_D = 5.6A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	7.6	—	S	V_{DS} = 5V, I_D = 7A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.7	1	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	404.5	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	51.8	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	45.1	—	pF	
Gate Resistance	R_g	—	1.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (10V)	Q_g	—	9.2	—	nC	V_{GS} = 10V, V_{DS} = 15V, I_D = 5.8A
Gate-Source Charge	Q_{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.4	—	ns	V_{GS} = 10V, V_{DS} = 15V, R_G = 3Ω, R_L = 2.6Ω
Turn-On Rise Time	t_R	—	6.18	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	13.92	—	ns	
Turn-Off Fall Time	t_F	—	2.84	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

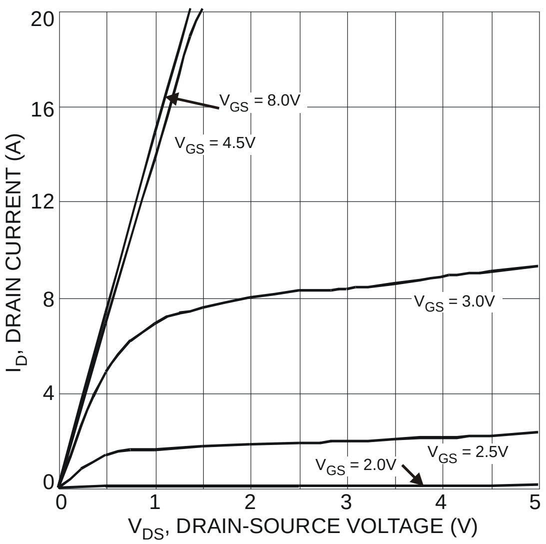


Fig. 1 Typical Output Characteristics

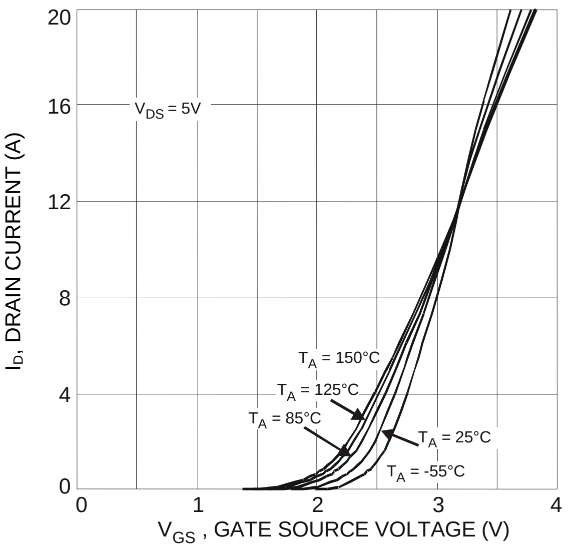


Fig. 2 Typical Transfer Characteristics

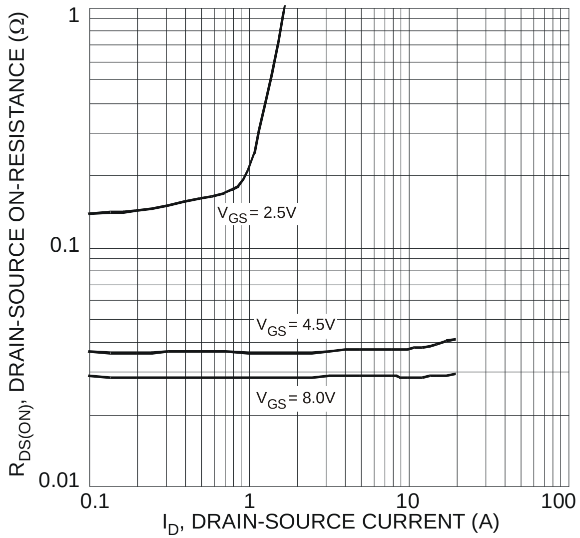


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

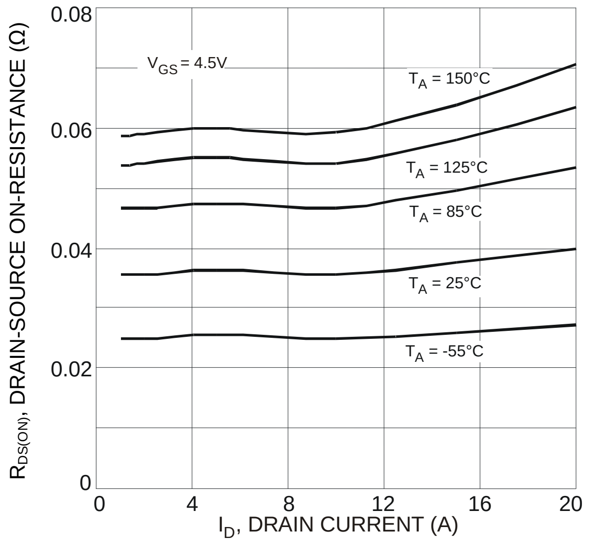


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

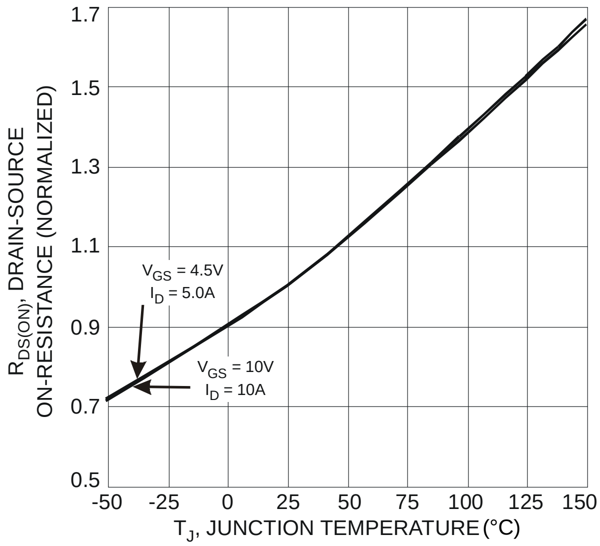


Fig. 5 On-Resistance Variation with Temperature

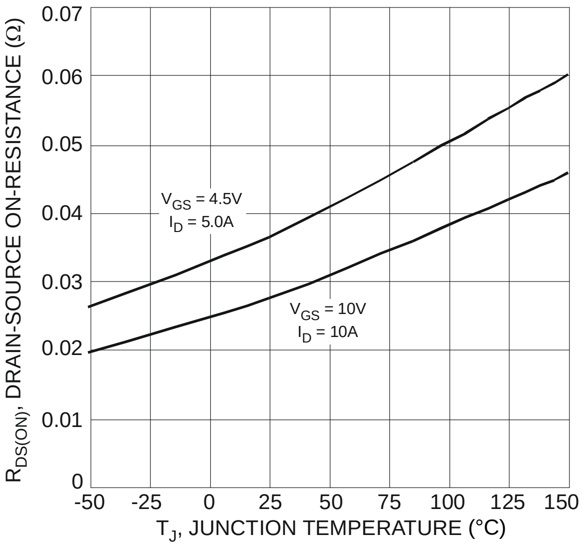


Fig. 6 On-Resistance Variation with Temperature

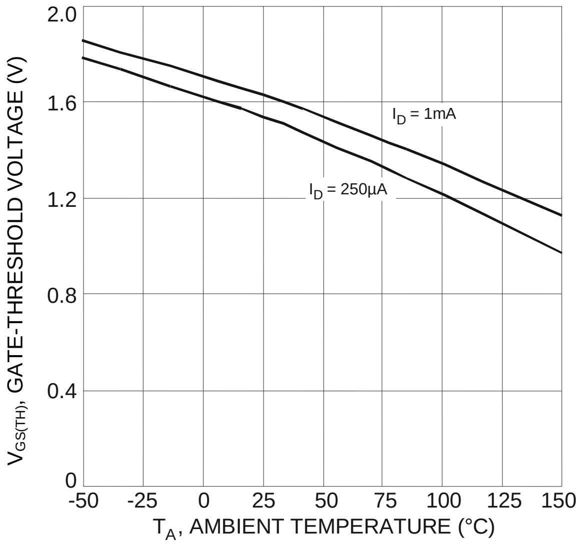


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

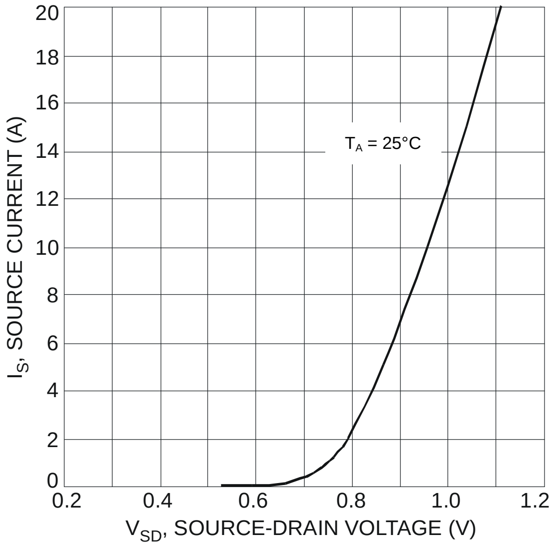


Fig. 8 Diode Forward Voltage vs. Current

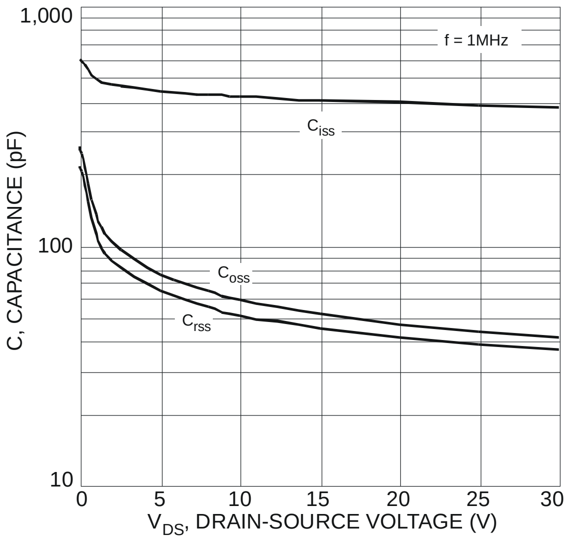


Fig. 9 Typical Capacitance

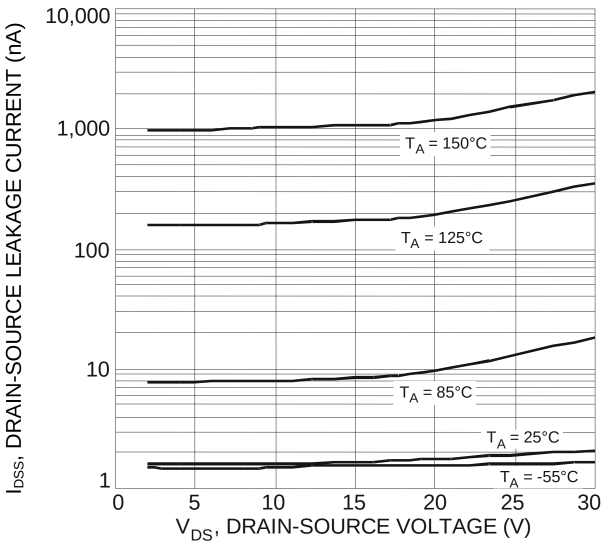


Fig. 10 Typical Drain-Source Leakage Current
vs. Drain-Source Voltage

Electrical Characteristics P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	-1.7	-2.2	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	30	39	mΩ	V_{GS} = -10V, I_D = -4.3A
			42	53		V_{GS} = -4.5V, I_D = -3.7A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	7	—	S	V_{DS} = -5V, I_D = -4.3A
Diode Forward Voltage (Note 7)	V_{SD}	—	-0.75	-1	V	V_{GS} = 0V, I_S = -1.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1002	—	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	125	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	118	—	pF	
Gate Resistance	R_g	—	13	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (-4.5V)	Q_g	—	10.1	—	nC	V_{GS} = -4.5V/-10V, V_{DS} = -15V, I_D = -6A
Total Gate Charge (-10V)	Q_g	—	21.1	—	nC	
Gate-Source Charge	Q_{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	10.1	—	ns	V_{GS} = -10V, V_{DS} = -15V, R_G = 6Ω , I_D = -1A
Turn-On Rise Time	t_R	—	6.5	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	50.1	—	ns	
Turn-Off Fall Time	t_F	—	22.2	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

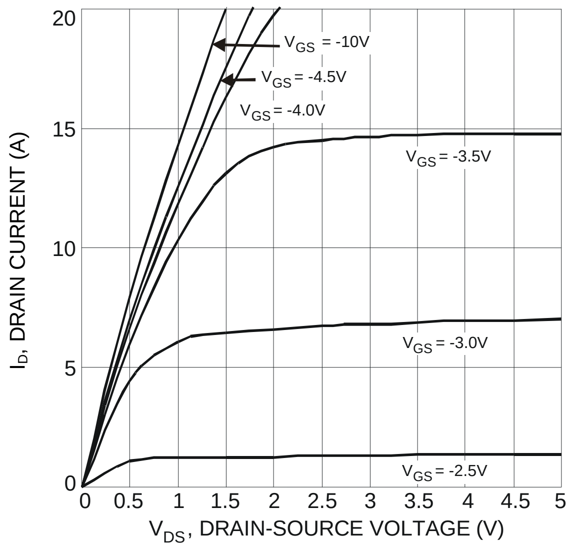


Fig. 11 Typical Output Characteristics

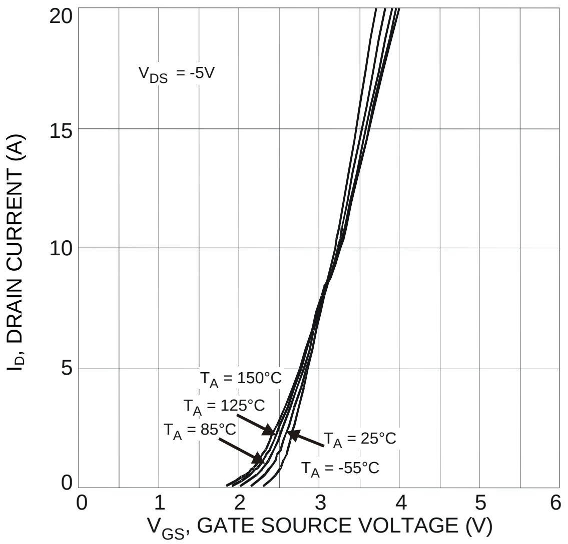


Fig. 12 Typical Transfer Characteristics

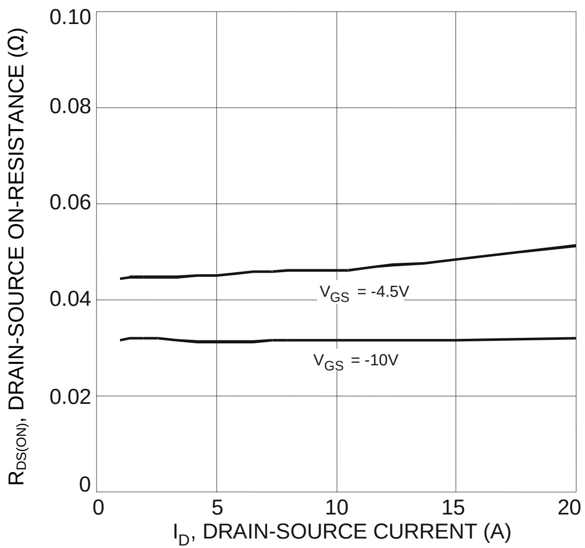


Fig. 13 Typical On-Resistance
vs. Drain Current and Gate Voltage

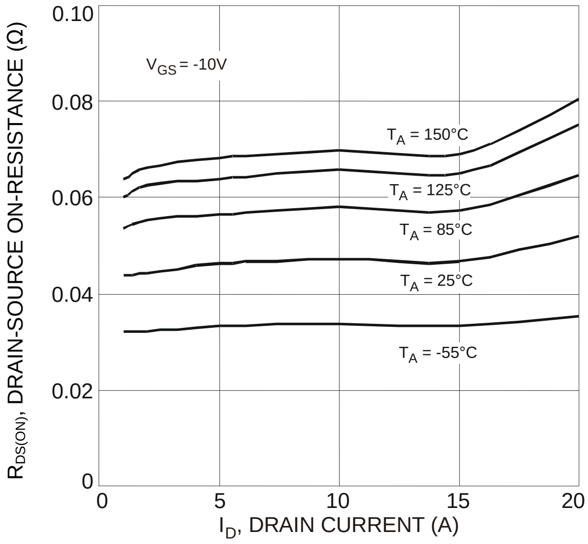


Fig. 14 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

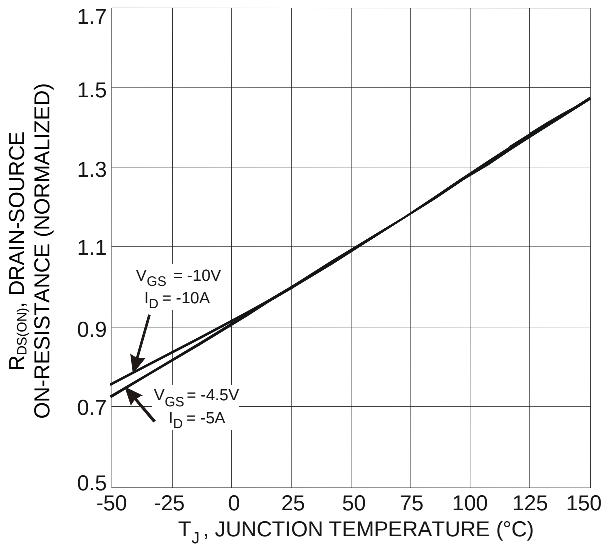


Fig. 15 On-Resistance Variation with Temperature

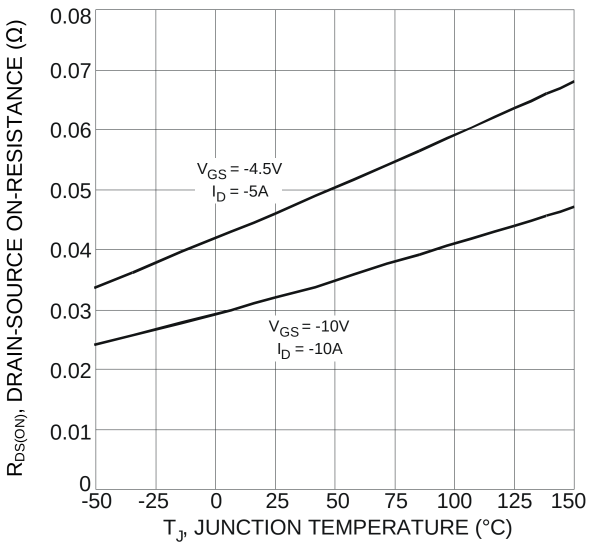


Fig. 16 On-Resistance Variation with Temperature

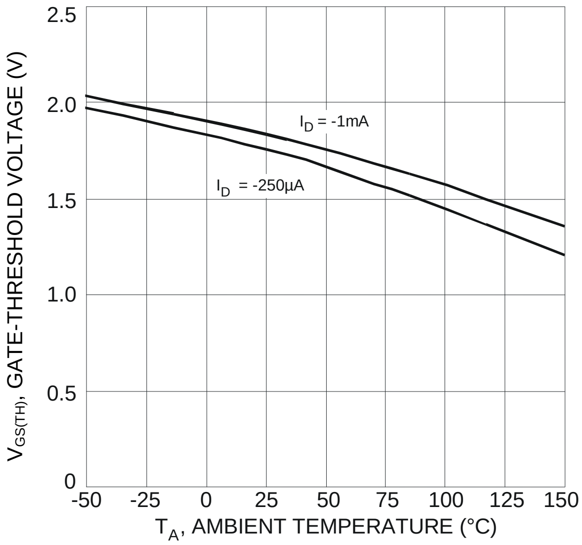


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

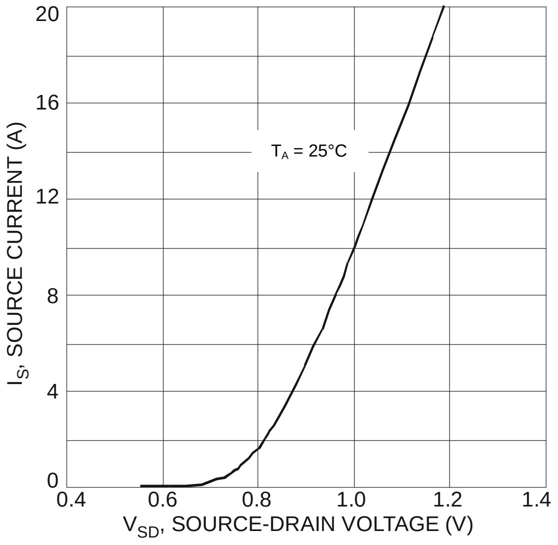


Fig. 18 Diode Forward Voltage vs. Current

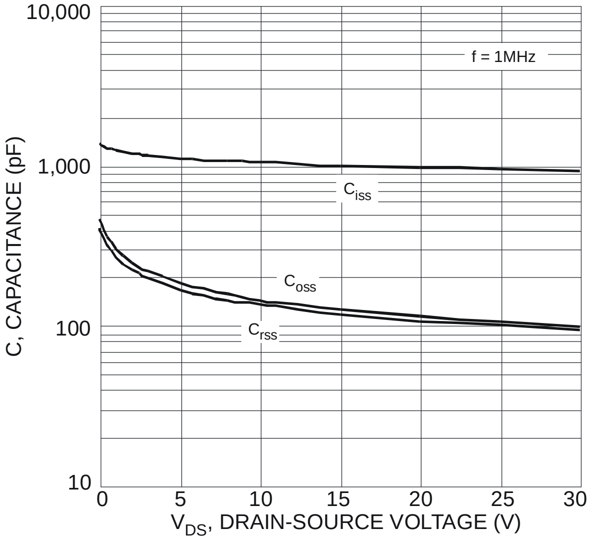


Fig. 19 Typical Capacitance

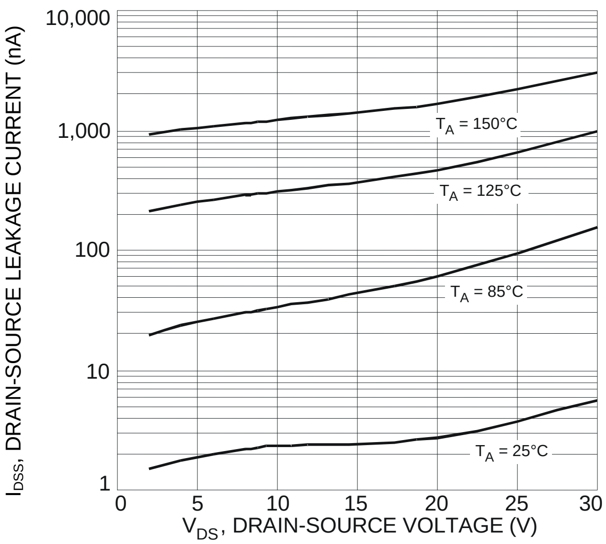
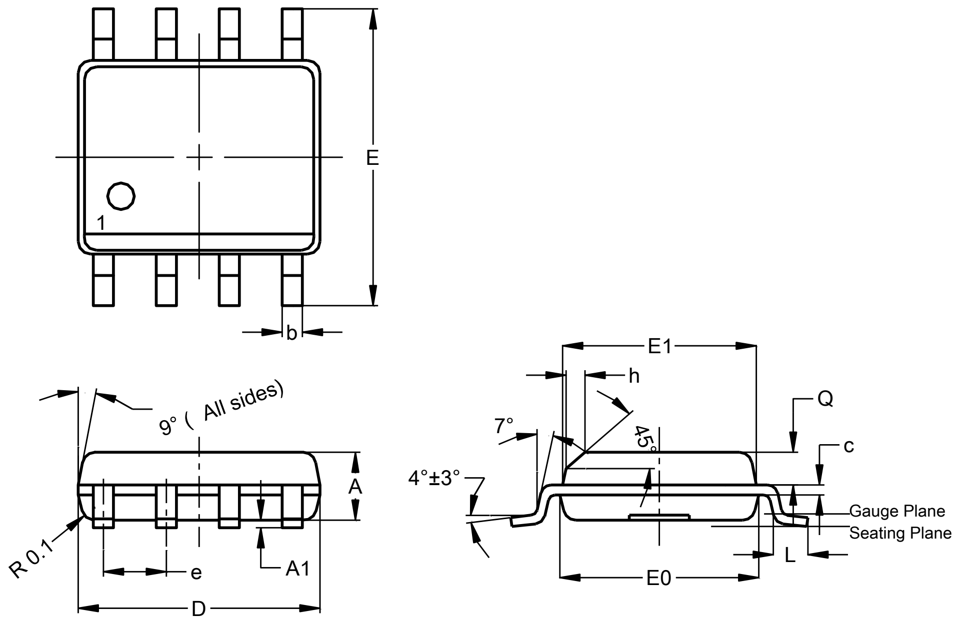


Fig. 20 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

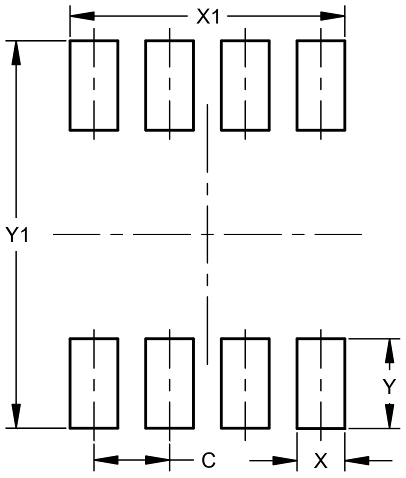
SO-8



SO-8			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50